

IN THE TITLE

Please delete the title in its entirety and insert – A METHOD OF FORMING A LOW-DIELECTRIC CONSTANT STRUCTURE WITH A MULTILAYER STACK OF THIN FILMS WITH PORES – therein.

IN THE CLAIMS

Claims 1-7 and 19-23 have been previously canceled without prejudice as being drawn to a non-elected invention.

Please amend claim 8.

Please enter the pending claims as follows:

1. - 7. (Canceled)

8. (Currently Amended) A process of forming a multilayer stack by alternately depositing and treating thin films comprising:

obtaining a substrate, said substrate comprising devices having features with a critical dimension;

depositing a first thin film on said substrate with a first precursor comprising a first set of organic components, said first thin film having a thickness that is less than about 20.0% of said critical dimension;

treating said first thin film to release said first set of organic components to leave a first set of pores;

depositing a second thin film over said first thin film with a second precursor comprising a second set of organic compounds, said second thin film having a thickness that is less than about 20.0% of said critical dimension; and

treating said second thin film to release said second set of organic components to leave a second set of pores.

9. (Original) The process of claim 8 wherein said first thin film comprises a first low-dielectric constant material.

10. (Original) The process of claim 9 wherein said second thin film comprises a second low-dielectric constant material.

11. (Original) The process of claim 9 wherein said first low-dielectric constant material comprises an inorganic oxide.

12. (Original) The process of claim 11 wherein said inorganic oxide comprises Silicon Dioxide or silica.

13. (Original) The process of claim 8 wherein said first thin film has a porosity of below about 30.0 volume %.

14. (Original) The process of claim 8 wherein said second thin film has a porosity of below about 30.0 volume %.

15. (Original) The process of claim 8 wherein said first set of pores are embedded within said first thin film.

16. (Original) The process of claim 8 wherein said second set of pores are embedded within said second thin film.

17. (Original) The process of claim 8 wherein said first set of pores are unconnected.

18. (Original) The process of claim 8 wherein said first set of pores have a size on the order of 0.3-3.0 nanometers.

19. – 23. (Canceled)